





### NPN PRE-BIASED 500 mA SURFACE MOUNT TRANSISTOR

### **Features**

- Epitaxial Planar Die Construction
- Complementary PNP Types Available (DDTB)
- · Built-In Biasing Resistors
- Lead, Halogen and Antimony Free, RoHS Compliant "Green" Device (Notes 2 and 3)

### **Mechanical Data**

Case: SOT-23

DDTD122LC

DDTD142JC

DDTD122TC

DDTD142TC

- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminal Connections: See Diagram
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Marking Information: See Table Below & Page 3
- Ordering Information: See Page 3Weight: 0.008 grams (approximate)
- P/N R1 (NOM) R2 (NOM) Type Code

0.22K $\Omega$ 

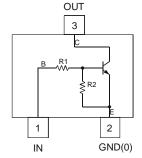
 $0.47 \text{K}\Omega$ 

0.22K $\Omega$ 

0.47K $\Omega$ 

→    ← A 
TOP VIEW B C
E G →

	SOT-23									
Dim	Min	Max								
Α	0.37	0.51								
В	1.20	1.40								
С	2.30	2.50								
D	0.89	1.03								
Е	0.45	0.60								
G	1.78	2.05								
Н	2.80	3.00								
J	0.013	0.10								
K	0.903	1.10								
L	0.45	0.61								
М	0.085	0.180								
α	0°	8°								
All Dir	nensions	s in mm								



Schematic and Pin Configuation

## Maximum Ratings @T<sub>A</sub> = 25°C unless otherwise specified

 $10 \text{K}\Omega$ 

 $10 \text{K}\Omega$ 

**OPEN** 

**OPEN** 

N75

N76

N77

N78

Characteristic		Symbol	Value	Unit
Supply Voltage, (3) to (2)		V <sub>CC</sub>	50	V
Input Voltage, (1) to (2)	DDTD122LC DDTD142JC	VIN	-5 to +6 -5 to +6	V
Input Voltage, (2) to (1)	DDTD122TC DDTD142TC	V <sub>EBO (MAX)</sub>	5	V
Output Current	All	Ic	500	mA
Power Dissipation	(Note 1)	P <sub>D</sub>	200	mW
Thermal Resistance, Junction to Ambient Air	(Note 2)	$R_{ heta JA}$	625	°C/W
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

Notes:

- 1. Mounted on FR4 PC Board with recommended pad layout at http://www.diodes.com/datasheets/ap02001.pdf.
- 2. No purposefully added lead. Halogen and Antimony Free.
- 3. Product manufactured with Data Čode V9 (week 33, 2008) and newer are built with Green Molding Compound. Product manufactured prior to Date Code V9 are built with Non-Green Molding Compound and may contain Halogens or Sb<sub>2</sub>O<sub>3</sub> Fire Retardants.



# **Electrical Characteristics** @TA = 25°C unless otherwise specified R1, R2 Types

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
Input Voltage	DDTD122LC DDTD142JC	V <sub>I(off)</sub>	0.3 0.3	_	_	V	V <sub>CC</sub> = 5V, I <sub>O</sub> = 100μA
	DDTD122LC DDTD142JC	V <sub>I(on)</sub>	_		2.0 2.0	V	V <sub>O</sub> = 0.3V, I <sub>O</sub> = 20mA V <sub>O</sub> = 0.3V, I <sub>O</sub> = 20mA
Output Voltage		V <sub>O(on)</sub>	_		0.3V	V	$I_O/I_I = 50$ mA/2.5mA
Input Current DDTD122LC DDTD142JC		I <sub>I</sub>	_		28 13	mA	V <sub>I</sub> = 5V
Output Current	Output Current		_	_	0.5	μА	$V_{CC} = 50V, V_I = 0V$
DC Current Gain DDTD122LC DDTD142JC		G <sub>l</sub>	56 56		_	_	V <sub>O</sub> = 5V, I <sub>O</sub> = 50mA
Gain-Bandwidth Product*		f⊤	_	200	_	MHz	$V_{CE} = 10V$ , $I_{E} = 5mA$ , $f = 100MHz$

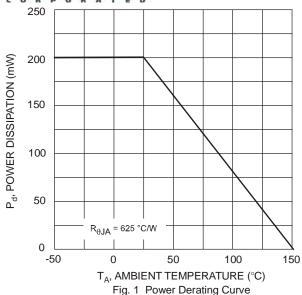
<sup>\*</sup> Transistor - For Reference Only

# Electrical Characteristics @T<sub>A</sub> = 25°C unless otherwise specified R1-Only, R2-Only Types

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	50		_	V	$I_C = 50\mu A$	
Collector-Emitter Breakdown Voltage	BV <sub>CEO</sub>	40	_	_	V	I <sub>C</sub> = 1mA	
Emitter-Base Breakdown Voltage DDTD122TC DDTD142TC		BV <sub>EBO</sub>	5		_	٧	$I_E = 50\mu A$ $I_E = 50\mu A$
Collector Cutoff Current		I <sub>CBO</sub>	_	_	0.5	μА	V <sub>CB</sub> = 50V
Emitter Cutoff Current DDTD122TC DDTD142TC		I <sub>EBO</sub>			0.5 0.5	μА	V <sub>EB</sub> = 4V
Collector-Emitter Saturation Voltage		V <sub>CE(sat)</sub>	_	_	0.3	٧	$I_C = 50$ mA, $I_B = 2.5$ mA
DC Current Transfer Ratio DDTD122TC DDTD142TC		h <sub>FE</sub>	100 100	250 250	600 600		$I_C = 5mA$ , $V_{CE} = 5V$
Gain-Bandwidth Product*		f <sub>T</sub>	_	200	_	MHz	$V_{CE} = 10V, I_{E} = -5mA, f = 100MHz$

<sup>\*</sup> Transistor - For Reference Only



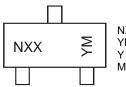


### **Ordering Information** (Note 4)

Device	Packaging	Shipping
DDTD122LC-7-F	SOT-23	3000/Tape & Reel
DDTD142JC-7-F	SOT-23	3000/Tape & Reel
DDTD122TC-7-F	SOT-23	3000/Tape & Reel
DDTD142TC-7-F	SOT-23	3000/Tape & Reel

Notes: 4. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

## Marking Information



NXX = Product Type Marking Code, See Table on Page 1

YM = Date Code Marking Y = Year ex: T = 2006 M = Month ex: 9 = September

Date Code Key

Year	2002	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012
Code	N	Р	R	S	Т	U	V	W	Х	Υ	Z

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

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